

Power MOSFETS (cont'd)

ECG Type	Description and Application	Transconductance gfs μmhos	Drain to Source Breakdown Voltage BV _{DSS}	Gate to Source Breakdown Voltage BV _{GS}	Continuous Drain Current I _D Amps	Gate to Source Threshold Voltage V _{GS} (th)	Drain to Source Resistance r _{DS(on)} Ohms	Input Cap C _{iss} pf	Device Dissipation @T _C =25° C P _D Watts	Package
										Case/Fig./Basing
ECG2388 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	5 Min	200 Min	±20 Max*	12.5	4 Max	.2 Max	1000 Typ	75 Max	TO-220 Fig. T41 
						td(off) = 120 ns, td(on) = 20 ns, tf = 60 ns, tr = 60 ns				
ECG2374 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	6 Min	200 Min	±20 Max*	18	4 Max	.18 Max	1300 Typ	125 Max	
						td(off) = 50 ns, td(on) = 20 ns, tf = 40 ns, tr = 60 ns				
ECG2900 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	6 Min	250 Min	±20 Max	14	4 Max	.28 Max	1300 Typ	125 Max	
						td(off) = 60 ns, td(on) = 20 ns, tf = 60 ns, tr = 30 ns				
ECG67 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	2 Min	400 Min	±20 Max*	5	4.5 Max	1.5 Max	1200 Max	75 Max	
						td(off) = 200 ns, td(on) = 50 ns, tf = 100 ns, tr = 100 ns				
ECG2391 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	2.1 Min	400 Min	±30 Max*	4	4 Max	1.8Max	500 Max	75 Max	
						td(off) = 65 ns, td(on) = 20 ns, tf = 40 ns, tr = 60 ns				
ECG2397 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	5 Min	400 Min	±30 Max*	10	4 Max	.5 Max	1800 Max	150 Max	
						td(off) = 200 ns, td(on) = 20 ns, tf = 75 ns, tr = 60 ns				
ECG2380 ▲ (Compl to ECG2381)	MOSFET, N-Ch, Enhancement Hi Speed Switch	1 Min	500 Min	±20 Max*	2	4.5 Max	4 Max	500 Max	75 Max	
						td(off) = 60 ns, td(on) = 40 ns, tf = 30 ns, tr = 60 ns				
ECG2381 ▲ (Compl to ECG2380)	MOSFET, N-Ch, Enhancement Hi Speed Switch	.5 Min	500 Min	±20 Max*	2	4.5 Max	6 Max	1000 Max	75 Max	
						td(off) = 150 ns, td(on) = 150 ns, tf = 50 ns, tr = 100 ns				
ECG2398 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	3.5 Min	500 Min	±30 Max*	5	4 Max	1.5 Max	1000 Max	100 Max	
						td(off) = 100 ns, td(on) = 10 ns, tf = 40 ns, tr = 45 ns				
ECG2385 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	5 Min	500 Min	±30 max*	8	4 Max	.8 Max	1800 Max	125 Max	
						td(off) = 250 ns, td(on) = 40 ns, tf = 90 ns, tr = 90 ns				
ECG2901 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	1 Min	600 Min	±20 Max*	2.5	4 Max	4 Max	500 Max	80 Max	
						td(off) = 20 ns, td(on) = 30 ns, tf = 30 ns, tr = 40 ns				
ECG2379 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	3 Min	600 Min	±20 Max*	6	4 Max	1.25 Max	1400 Typ	100 Max	
						td(off) = 85 ns, td(on) = 40 ns, tf = 20 ns, tr = 25 ns				

* Warning - Exceeding BV_{GS} maximum will result in permanent damage to the gate region oxide layer.

▲ Refer to MOSFET Handling Precautions - Page 1-34

Package Outlines - See Page 1-91